

DHG60U1200LB

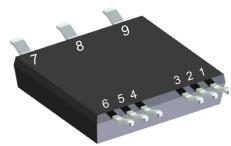
Sonic Fast Recovery Diode

V_{RRM}	=	1200 V		
I _{dav}	=	60 A		
t _{rr}	=	160 ns		

High Performance Fast Recovery Diode Low Loss and Soft Recovery 3~ Rectifier Bridge

Part number

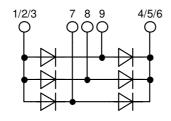
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Backside: isolated



20190404d



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviourAvalanche voltage rated for reliable
- operationSoft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SMPD

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
 - Soldering pins for PCB mounting
 - Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

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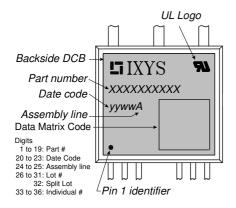
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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blockin	$T_{VJ} = 25^{\circ}C$			1200	V	
V _{RRM}	max. repetitive reverse blocking vo	oltage	$T_{vJ} = 25^{\circ}C$			1200	V
I _R	reverse current, drain current	V _R = 1200 V	$T_{VJ} = 25^{\circ}C$			50	μA
		V _R = 1200 V	$T_{vJ} = 125^{\circ}C$			0.5	mA
V _F	forward voltage drop	I _F = 20 A	$T_{VJ} = 25^{\circ}C$			2.00	V
		I _F = 60 A				2.92	V
		I _F = 20 A	T _{vJ} = 125°C			1.94	V
		$I_{F} = 60 \text{ A}$				3.15	V
I DAV	bridge output current	$T_c = 80^{\circ}C$	T _{vJ} = 150°C			60	А
		rectangular $d = \frac{1}{3}$					
V _{F0}	threshold voltage	$T_{vJ} = 150^{\circ}C$			1.35	V	
r _F	slope resistance } for power los				29	mΩ	
R _{thJC}	thermal resistance junction to case					1.2	K/W
R _{thCH}	thermal resistance case to heatsink				0.40		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			100	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_{R} = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			200	Α
C	junction capacitance	$V_{R} = 600 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		11		pF
I _{RM}	max. reverse recovery current		$T_{vJ} = 25 °C$		19		Α
		$I_F = 20 \text{ A}; V_R = 600 \text{ V}$	T _{vJ} = 125 °C		25		Α
t _{rr}	reverse recovery time	I _F = 20 A; V _R = 600 V -di _F /dt = 600 A/μs	$T_{VJ} = 25 °C$		160		ns
)		T _{vJ} = 125 °C		280		ns

20190404d



Package SMPD				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
	RMS current	per terminal				100	Α
T _{vj}	virtual junction temperature			-55		150	°C
T_{op}	operation temperature			-55		125	°C
T _{stg}	storage temperature			-55		150	°C
Weight					8.5		g
F _c	mounting force with clip			40		130	Ν
d _{Spp/App}	creepage distance on surface striking distance through air		terminal to terminal	1.6			mm
d _{Spb/Apb}			terminal to backside	4.0			mm
V	isolation voltage t = 1 second t = 1 minute	t = 1 second		3000			۷
		50/60 Hz, RMS; liso∟ ≤ 1 mA	2500			v	



Part description



- H = Sonic Fast Recovery Diode
- G = extreme fast
- 60 = Current Rating [A]
- U = 3~ Rectifier Bridge
- 1200 = Reverse Voltage [V]
- LB = SMPD-B

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG60U1200LB-TUB	DHG60U1200LB-TUB	Tube	20	524936
Alternative	DHG60U1200LB-TRR	DHG60U1200LB	Tape & Reel	200	524950

Equivalent Circuits for Simulation		* on die level	$T_{vJ} = 150 \ ^{\circ}C$	
	- Ro-	Fast Diode		
V _{0 max}	threshold voltage	1.35		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	27		mΩ

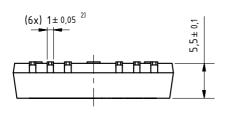
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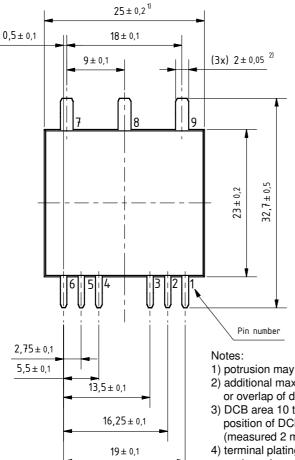
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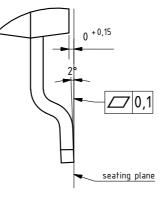
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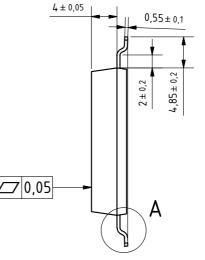
Outlines SMPD





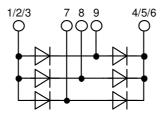
A (8:1)





1) potrusion may add 0.2 mm max. on each side

- 2) additional max. 0.05 mm per side by punching misalignement or overlap of dam bar or bending compression
- DCB area 10 to 50 μm convex; position of DCB area in relation to plastic rim: ±25 μm (measured 2 mm from Cu rim)
- 4) terminal plating: 0.2 1 μm Ni + 10 25 μm Sn (gal v.) cutting edges may be partially free of plating

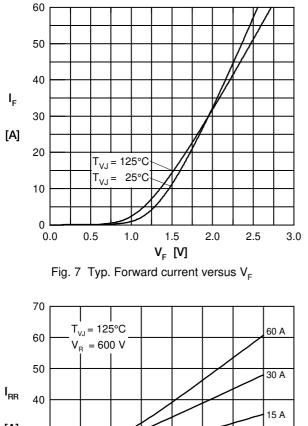


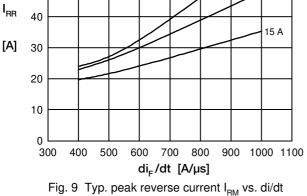
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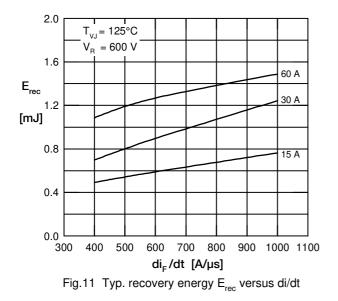
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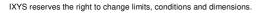


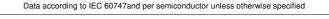
Fast Diode

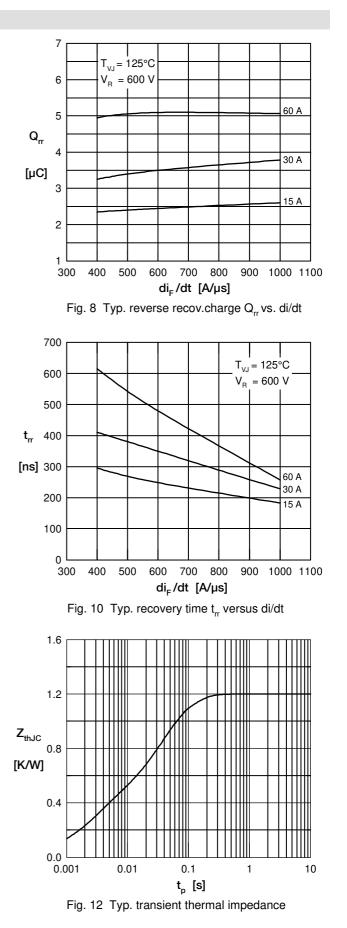












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